

July 1998

## **DS36276**

## **FAILSAFE Multipoint Transceiver**

### **General Description**

The DS36276 FAILSAFE Multipoint Transceiver is designed for use on bi-directional differential busses. It is compatible with existing TIA/EIA-485 transceivers, however, it offers an additional feature not supported by standard transceivers.

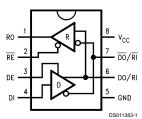
The FAILSAFE feature guarantees the receiver output to a known state when the Interface is in the following conditions: Floating Line, Idle Line (no active drivers), and Line Fault conditions (open or short). The receiver output is in a  $\ensuremath{\mathsf{HIGH}}$ state for the following conditions: OPEN Inputs, Terminated Inputs (50 $\Omega$ ), and SHORTED Inputs.

FAILSAFE is a highly desirable feature when the transceivers are used with Asynchronous Controllers such as UARTs.

### **Features**

- FAILSAFE receiver, RO = HIGH for:
  - OPEN inputs
- Terminated inputs
- SHORTED inputs
- Compatible with popular interface standards:
  - TIA/EIA-485 (RS-485)
  - TIA/EIA-422-À (RS-422-A)
- CCITT Recommendation V.11
- Bi-Directional Transceiver
  - Designed for multipoint transmission
- Separate driver input, driver enable, receiver enable, and receiver output for maximum flexibility
- Wide bus common mode range
- (-7V to +12V)
- Pin compatible with: DS75176B, DS96176, DS3695 and SN75176A and B
- Available in SOIC package

## **Connection and Logic Diagram**



Order Number DS36276M See NS Package Number M08A

### **Truth Tables**

### **Driver**

	Inputs		Outputs			
RE	DE	DI	DO/RI	DO /RI		
Х	Н	Н	Н	L		
X	Н	L	L	Н		
X	L	Х	Z	Z		

### Receiver

	Inputs		
RE	DE	RI– <del>R</del> I	RO
L	L	≥0V	Н
L	L	≤–500 mV	L
Н	X	x	z

### **Receiver FAILSAFE**

	Inputs				
RE	DE	RI–RI	RO		
L	L	SHORTED	Н		
L	L	OPEN	Н		
Н	Х	X	Z		

TRI-STATE® is a registered trademark of National Semiconductor Corporation.

## Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V<sub>CC</sub>) 7V Input Voltage (DE,  $\overline{\text{RE}}$  , and DI) 5.5V Driver Output Voltage/

Receiver Input Voltage -10V to +15V 5.5V

Receiver Output Voltage (RO) Maximum Package Power Dissipation @ +25°C

M Package

(derate 5.8 mW/°C above +25°C) 726 mW -65°C to +150°C Storage Temperature Range

Lead Temperature (Soldering 4 260°C Max Junction Temperature 150°C ESD Rating (HBM, 1.5  $k\Omega,\,100$  $\geq 6.0 \text{ kV}$ 

### **Recommended Operating Conditions**

Min	Max	Units
4.75	5.25	V
-7	+12	V
0	+70	°C
	4.75 -7	4.75 5.25 -7 +12

## Electrical Characteristics (Notes 2, 4)

Over recommended Supply Voltage and Operating Temperature ranges, unless otherwise specified.

Symbol	Parameter	Cond	litions		Min	Тур	Max	Units
DRIVER (	CHARACTERISTICS	•				•		
V <sub>OD</sub>	Differential Output Voltage	I <sub>O</sub> = 0 mA (No Load)		1.5	4.8	6.0	V	
V <sub>oDO</sub>	Output Voltage	I <sub>O</sub> = 0 mA (Output t	o GND)		0		6.0	V
V <sub>oDO</sub>	Output Voltage	1			0		6.0	V
V <sub>T1</sub>	Differential Output Voltage	$R_L = 54\Omega (485)$	(Figure 1)		1.5	2.0	5.0	V
	(Termination Load)	$R_L = 100\Omega (422)$			2.0	2.3	5.0	V
$\Delta V_{T1}$	Balance of V <sub>T1</sub>	$R_L = 54\Omega$	(Note 3)		-0.2	0.07	+0.2	V
	$ V_{T1}  -  \overline{V}_{\overline{11}} $	$R_L = 100\Omega$			-0.2	0.07	+0.2	V
Vos	Driver Common Mode	$R_L = 54\Omega$	(Figure 1)		0	2.5	3.0	V
	Output Voltage	$R_L = 100\Omega$			0	2.3	3.0	V
$\Delta V_{OS}$	Balance of V <sub>OS</sub>	$R_L = 54\Omega$	(Note 3)		-0.2	0.08	+0.2	V
	$ V_{OS}  -  \overline{V}_{OS} $	$R_L = 100\Omega$			-0.2	0.08	+0.2	V
I <sub>OSD</sub>	Driver Short-Circuit	V <sub>O</sub> = +12V	(Figure 3)			134	290	mA
	Output Current	$V_O = V_{CC}$				140		mA
		V <sub>O</sub> = 0V	]			-140		mA
		V <sub>O</sub> = -7V				-180	-290	mA
RECEIVE	R CHARACTERISTICS	•	•			•		
V <sub>TH</sub>	Differential Input High Threshold Voltage (Note 5)	$V_{O} = V_{OH}, I_{O} = -0.4$ $-7V \le V_{CM} \le +12V$	ł mA			-0.18	0	V
$V_{TL}$	Differential Input Low Threshold Voltage (Note 5)	$V_{O} = V_{OL}, I_{O} = 8.0 \text{ I}$ $-7V \le V_{CM} \le +12V$	mA		-0.5	-0.23		V
V <sub>HST</sub>	Hysteresis (Note 6)	V <sub>CM</sub> = 0V				50		mV
I <sub>IN</sub>	Line Input Current	Other Input = 0V	V <sub>I</sub> = +12V			0.7	1.0	mA
	$(V_{CC} = 4.75V, 5.25V, 0V)$	DE = V <sub>IH</sub> (Note 7)	V <sub>I</sub> = -7V			-0.5	-0.8	mA
I <sub>OSR</sub>	Short Circuit Current	V <sub>O</sub> = 0V		RO	-5.0	-30	-85	mA
l <sub>oz</sub>	TRI-STATE® Leakage Current	$V_{\rm O} = 0.4 \text{ to } 2.4 \text{V}$			-20		+20	μA
$V_{OH}$	Output High Voltage	$V_{ID} = 0V, I_{OH} = -0.4$	1 mA		2.5	3.5		V
	(Figure 12)	V <sub>ID</sub> = OPEN, I <sub>OH</sub> =	–0.4 mA		2.5	3.5		V
V <sub>OL</sub>	Output Low Voltage	$V_{ID} = -0.5V, I_{OL} = +$	-8 mA			0.25	0.6	V
	(Figure 12)	$V_{ID} = -0.5V, I_{OL} = +$	-16 mA			0.35	0.7	V
R <sub>IN</sub>	Input Resistance				12	19		kΩ

## Electrical Characteristics (Notes 2, 4) (Continued)

Over recommended Supply Voltage and Operating Temperature ranges, unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Units		
DEVICE C	DEVICE CHARACTERISTICS								
V <sub>IH</sub>	High Level Input Voltage		DE,	2.0		V <sub>cc</sub>	V		
V <sub>IL</sub>	Low Level Input Voltage		RE,	GND		0.8	V		
I <sub>IH</sub>	High Level Input Current	V <sub>IH</sub> = 2.4V	or DI			20	μA		
I <sub>IL</sub>	Low Level Input Current	V <sub>IL</sub> = 0.4V				-100	μA		
V <sub>CL</sub>	Input Clamp Voltage	I <sub>CL</sub> = -18 mA			-0.75	-1.5	V		
I <sub>cc</sub>	Output Low Voltage	$DE = 3V$ , $\overline{RE} = 0V$ , $DI = 0V$			42	60	mA		
I <sub>CCR</sub>	Supply Current	$DE = 0V, \overline{RE} = 0V, DI = 0V$			28	45	mA		
I <sub>CCD</sub>	(No Load)	DE = 3V, RE = 3V, DI = 0V			43	60	mA		
I <sub>ccx</sub>		$DE = 0V, \overline{RE} = 3V, DI = 0V$			31	50	mA		

## **Switching Characteristics** (Note 4)

Over recommended Supply Voltage and Operating Temperature ranges, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
DRIVER CH	IARACTERISTICS					
t <sub>PLHD</sub>	Diff. Prop. Delay Low to High	$R_L = 54\Omega$	7	21	60	ns
t <sub>PHLD</sub>	Diff. Prop. Delay High to Low	C <sub>L</sub> = 50 pF	7	19	60	ns
t <sub>SKD</sub>	Diff. Skew ( t <sub>PLHD</sub> -t <sub>PHLD</sub>  )	$C_D = 50 \text{ pF}$		2	10	ns
t <sub>r</sub>	Diff. Rise Time	(Figures 4, 5)		12	50	ns
t <sub>f</sub>	Diff. Fall Time			12	50	ns
t <sub>PLH</sub>	Prop. Delay Low to High	$R_L = 27\Omega, C_L = 15 pF$		22	45	ns
t <sub>PHL</sub>	Prop. Delay High to Low	(Figures 6, 7)		22	45	ns
t <sub>PZH</sub>	Enable Time Z to High	$R_L = 110\Omega$		32	55	ns
t <sub>PZL</sub>	Enable Time Z to Low	C <sub>L</sub> = 50 pF		32	65	ns
t <sub>PHZ</sub>	Disable Time High to Z	(Figure 8 – Figure 11)		22	55	ns
t <sub>PLZ</sub>	Disable Time Low to Z	1		16	55	ns
RECEIVER	CHARACTERISTICS		•		•	
t <sub>PLH</sub>	Prop. Delay Low to High	$V_{ID} = -1.5V \text{ to } +1.5V$	15	40	70	ns
t <sub>PHL</sub>	Prop. Delay High to Low	C <sub>L</sub> = 15 pF	15	42	70	ns
t <sub>sk</sub>	Skew ( t <sub>PLH</sub> -t <sub>PHL</sub>  )	(Figures 13, 14)		2	15	ns
t <sub>PZH</sub>	Enable Time Z to High	C <sub>L</sub> = 15 pF (Figures 15, 16)		15	50	ns
t <sub>PZL</sub>	Enable Time Z to Low			17	50	ns
t <sub>PHZ</sub>	Disable Time High to Z			24	50	ns
t <sub>PLZ</sub>	Disable Time Low to Z			19	50	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" specify conditions for device operation.

Note 2: Current into device pins is defined as positive. Current out of device pins is defined as negative. All voltages are referenced to ground unless otherwise speci-

 $\textbf{Note 3:} \quad \Delta \; |V_{T1}| \; \text{and} \; \Delta \; |V_{OS}| \; \text{are changes in magnitude of} \; V_{T1} \; \text{and} \; V_{OS}, \; \text{respectively, that occur when the input changes state}.$ 

**Note 4:** All typicals are given for V  $_{CC}$  = 5.0V and  $T_A$  = +25°C.

Note 5: Threshold parameter limits specified as an algebraic value rather than by magnitude.

Note 6: Hysteresis defined as  $V_{HST} = V_{TH} - V_{TL}$ .

Note 7:  $I_{\text{IN}}$  includes the receiver input current and driver TRI-STATE leakage current.

## **Parameter Measurement Information**

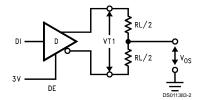


FIGURE 1. Driver  $\rm V_{T1}$  and  $\rm V_{OS}$  Test Circuit

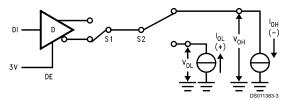


FIGURE 2. Driver  $\rm V_{OH}$  and  $\rm V_{OL}$  Test Circuit

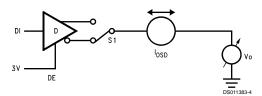


FIGURE 3. Driver Short Circuit Test Circuit

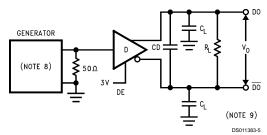


FIGURE 4. Driver Differential Propagation Delay and Transition Time Test Circuit

## Parameter Measurement Information (Continued)

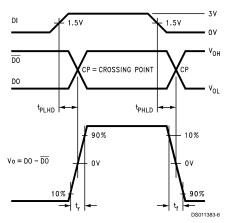


FIGURE 5. Driver Differential Propagation Delays and Transition Times

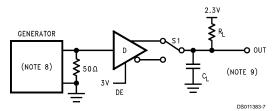


FIGURE 6. Driver Propagation Delay Test Circuit

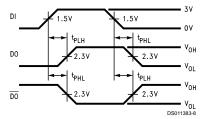
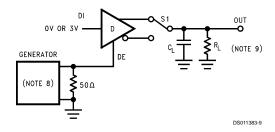


FIGURE 7. Driver Propagation Delays



S1 to  $\overline{DO}$  for DI = 3V S1 to  $\overline{DO}$  for DI = 0V

FIGURE 8. Driver TRI-STATE Test Circuit ( $t_{\rm PZH},\,t_{\rm PHZ}$ )

## Parameter Measurement Information (Continued)

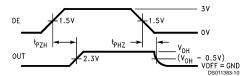
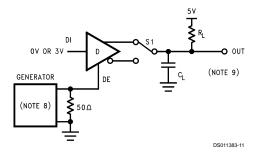


FIGURE 9. Driver TRI-STATE Delays ( $t_{\rm PZH},\,t_{\rm PHZ}$ )



S1 to  $\overline{DO}$  for DI = 0V S1 to  $\overline{DO}$  for DI = 3V

FIGURE 10. Driver TRI-STATE Test Circuit ( $t_{\text{PZL}},\,t_{\text{PLZ}}$ )

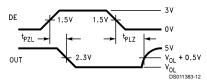


FIGURE 11. Driver TRI-STATE Delays  $(t_{PZL},\,t_{PLZ})$ 

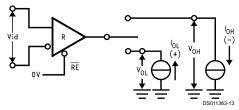


FIGURE 12. Receiver  $V_{OH}$  and  $V_{OL}$ 

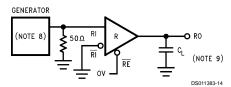
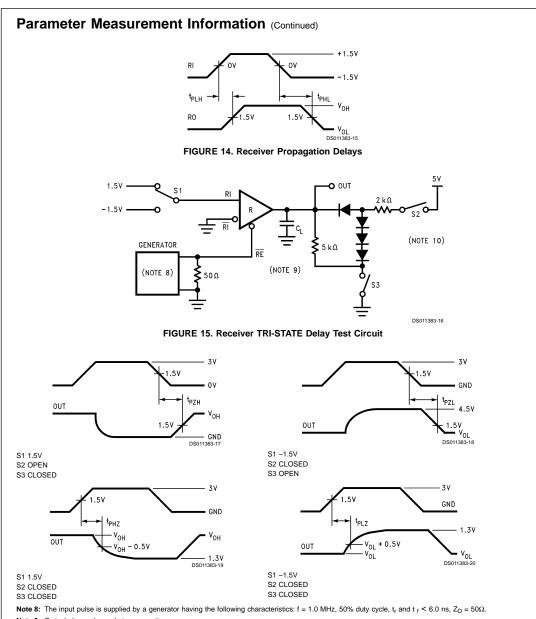


FIGURE 13. Receiver Propagation Delay Test Circuit

www.national.com



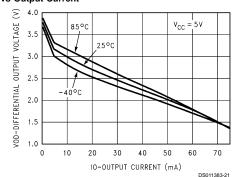
Note 9: C<sub>L</sub> includes probe and stray capacitance.

Note 10: Diodes are 1N916 or equivalent.

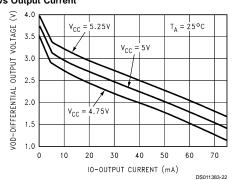
FIGURE 16. Receiver Enable and Disable Timing

## **Typical Performance Characteristics**

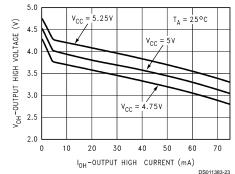
# Differential Output Voltage vs Output Current



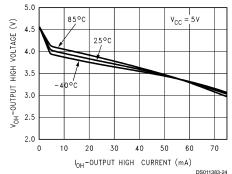
# Differential Output Voltage vs Output Current



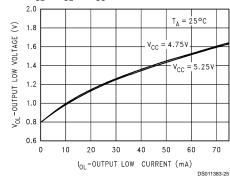
### Driver $\rm V_{OH}$ vs $\rm I_{OH}$ vs $\rm V_{CC}$



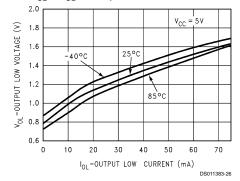
### Driver $V_{OH}$ vs $I_{OH}$ vs Temperature



### Driver $V_{\rm OL}$ vs $I_{\rm OL}$ vs $V_{\rm CC}$

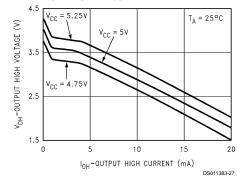


### Driver $V_{OL}$ vs $I_{OL}$ vs Temperature

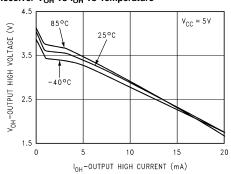


## **Typical Performance Characteristics** (Continued)

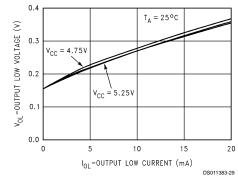
### Receiver V<sub>OH</sub> vs I<sub>OH</sub> vs V<sub>CC</sub>



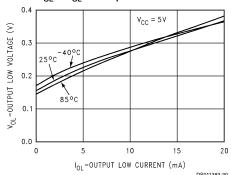
### Receiver $V_{OH}$ vs $I_{OH}$ vs Temperature



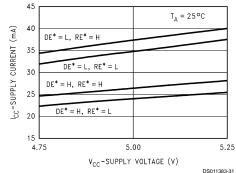
## Receiver $V_{\rm OL}$ vs $I_{\rm OL}$ vs $V_{\rm CC}$



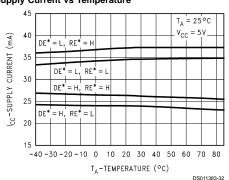
### Receiver $\mathbf{V}_{\mathrm{OL}}$ vs $\mathbf{I}_{\mathrm{OL}}$ vs Temperature



### Supply Currrent vs Supply Voltage

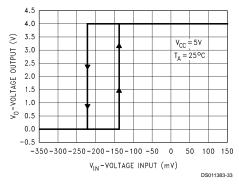


### **Supply Current vs Temperature**



## Typical Performance Characteristics (Continued)

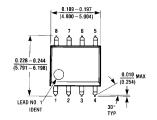
Voltage Output vs Voltage Input (Hysteresis)

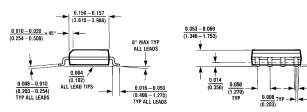


10

www.national.com

### Physical Dimensions inches (millimeters) unless otherwise noted





Order Number DS36276M NS Package Number M08A

### LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF NATIONAL SEMI-CONDUCTOR CORPORATION. As used herein:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



National Semiconductor

National Semiconductor
Corporation
Americas
Tel: 1-800-272-9959
Fax: 1-800-737-7018
Email: support@nsc.com

www.national.com

National Semiconductor

Europe
Fax: +49 (0) 1 80-530 85 86
E⊤mil: europe.support@nsc.con
Deutsch Tel: +49 (0) 1 80-530 85 85
English Tel: +49 (0) 1 80-532 78 32
Français Tel: +49 (0) 1 80-532 93 58
Italiano Tel: +49 (0) 1 80-534 16 80

National Semiconductor Asia Pacific Custome Response Group Tel: 65-2544466 Fax: 65-2504466 Email: sea.support@nsc.com National Semiconductor Japan Ltd.
Tel: 81-3-5639-7560
Fax: 81-3-5639-7507

National does not assume any responsibility for use of any circuitry described, no circuit patent licenses are implied and National reserves the right at any time without notice to change said circuitry and specifications,